## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE PATENT APPLICATION

In re Application of:

Chen et al.

Atty. Docket: TI-37133

**TBD** Serial No.:

Art Unit: TBD

Filed:

Herewith

Examiner: TBD

For:

METHOD TO FORM SHALLOW TRENCH ISOLATION WITH

ROUNDED UPPER CORNER FOR ADVANCED

SEMICONDUCTOR CIRCUITS

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

## INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97 & 1.98

Sir:

Applicants wish to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO-1449. Pursuant to the new rule, copies of only the non-patent literature cited are being submitted. Please charge any necessary fees to the deposit account of Texas Instruments Incorporated, Account No. 20-0668. Charge any additional fee required or credit any overpayment to the same.

Texas Instruments Incorporated P. O. Box 655474, M/S 3999 Dallas, Texas 75265 (972) 917-5355

Attorney for Applicant(s)

Respectfully submitted,

Reg. No. 52,305

LIST OF DOCUMENTS CITED BY APPLICAN'T    APPLICANT   Chen et al.   FILING DATE   GROUP   Herewith   TBD	FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE				ATTY. DOCKET NO.			SERIAL NO.			
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